

DESCRIPTION

The A93C66 provides 4096 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 256 words of 16 bits each, when the ORG pin is connected to Vcc and 512 words of 8 bits each when it is tied to ground.

The A93C66 is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a Read instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate erase cycle is required before write. The Write cycle is only enabled when it is in the Erase/Write Enable state. When CS is brought "high" following the initiation of a write cycle, the DO pin outputs the Ready/Busy status.

The A93C66 is available in SOP8 and TSSOP8 Package.

FEATURES

- Three-wire Serial Interface
- $V_{CC} = 1.8V \text{ to } 5.5V$
- Sequential Read Operation
- 2 MHz Clock Rate (5V) Compatibility
- Self-timed Write Cycle (5 ms max)
- 1 Million Write Cycles guaranteed
- Data Retention > 100 Years
- Available in SOP8 and TSSOP8 Package

ORDERING INFORMATION

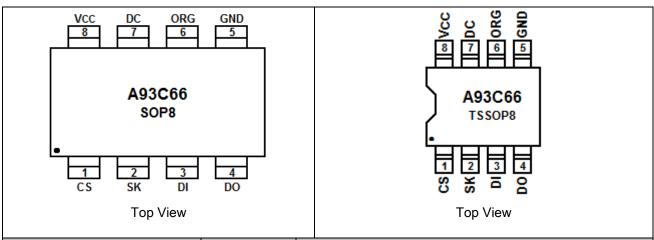
Package Type	Part Number				
		A93C66M8R			
CODe	MO	A93C66M8U			
SOP8	M8	A93C66M8VR			
		A93C66M8VU			
T000D0	TMX8	A93C66TMX8R			
		A93C66TMX8U			
TSSOP8		A93C66TMX8VR			
		A93C66TMX8VU			
	R: Tape & Reel				
Note	U: Tube				
	V: Halogen free Package				
AiT provides all RoHS products					

suffix "V" means Halogen free Package

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PIN DESCRIPTION



Pin#		Cumahal	Functions	
SOP8	TSSOP8	Symbol	Functions	
1	1	CS	Chip Select	
2	2	SK	Serial Data Clock	
3	3	DI	Serial Data Input	
4	4	DO	Serial Data Output	
5	5	GND	Ground	
6	6	ORG	Internal Organization	
7	7	DC	Don't Connect	
8	8	Vcc	Power Supply	

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ABSOLUTE MAXIMUM RATINGS

DC Supply Voltage	-0.3V ~ +6.5V
Input/ Output Voltage	GND-0.3V ~ V _{CC} +0.3V
Operating Ambient Temperature	-40°C ~ +85°C
Storage Temperature	-65°C ∼ +150°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

PIN CAPACITANCE

T_A=25°C, f=1.0MHz, V_{CC}=+1.8V (Unless otherwise specified)

PARAMETER	SYMBOL	MAX	UNIT	CONDITION
Output Capacitance (DO)	Соит	5	pF	V _{OUT} =0V
Input Capacitance (CS, SK, DI)	C _{IN}	5	pF	V _{IN} =0V

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DC ELECTRICAL CHARACTERISTICS

 T_A =-40°C to +85°C, V_{CC} =+1.8V to +5.5V (Unless otherwise specified)

Parameter	Symbo	Condition			MIN	TYP	MAX	Unit
Supply Voltage	V _{CC1}			1.8	-	5.5	V	
Supply Voltage	V _{CC2}				2.7	-	5.5	V
Supply Voltage	Vccз				4.5	-	5.5	V
0 1 0 1		., 50.,	Read	at 1.0MHz	-	0.2	2.0	
Supply Current	Icc	V _{CC} =5.0V	Write	Write at 1.0MHz		0.9	3.0	mA
Standby Current	I _{SB1}	V _{CC} =1.8V			-	-	1.0	
Standby Current	I _{SB2}	Vcc=2.7V,	CS=0\	/	-	-	1.0	μΑ
Standby Current	I _{SB3}	V _{CC} =5.0V			-	-	1.0	
Input Leakage NOTE1	I₁∟	V _{IN} =0V to V _{CC}			-	0.1	1.0	μΑ
Input Leakage NOTE2	I₁∟	V _{IN} =0V to V _{CC}			-	2.0	3.0	μΑ
Output Leakage	loL	V _{IN} =0V to V _C	С		-	0.1	1.0	uA
Input Low VoltageNOTE3	V _{IL1}	0.71/ 11/	5.5)/		-0.3	-	0.8	.,
Input High VoltageNOTE3	V _{IH1}	2.7V ≤ V _{CC} ≤	5.5V		2.0	-	V _{CC} +0.3	V
Input Low VoltageNOTE3	V _{IL2}	4.007.407.4	0.71/		-0.5	-	Vcc+0.3	.,
Input High VoltageNOTE3	V _{IH2}	1.8V ≤ V _{CC} ≤ 2.7V			Vccx0.7	-	Vcc+0.3	V
Output Low Voltage	V _{OL1}	2.7V ≤ V _{CC} ≤ 5.5V		I _{OL} = 2.1mA	-	-	0.4	M
Output High Voltage	V _{OH1}			I _{OH} = -0.4mA	2.4	-	-	V
Output Low Voltage	V _{OL2}	1.8V ≤ V _{CC} ≤ 2.7V		I _{OL} =0.15mA	-	-	0.2	V
Output High Voltage	V _{OH2}			I _{OH} =-100uA	Vcc-0.2	-	-	V

NOTE1: DI、CS、SK input pin

NOTE2: ORG input pin

NOTE3: $V_{\text{\scriptsize{IL}}}$ min and $V_{\text{\scriptsize{IH}}}$ max are reference only and are not tested.

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AC ELECTRICAL CHARACTERISTICS

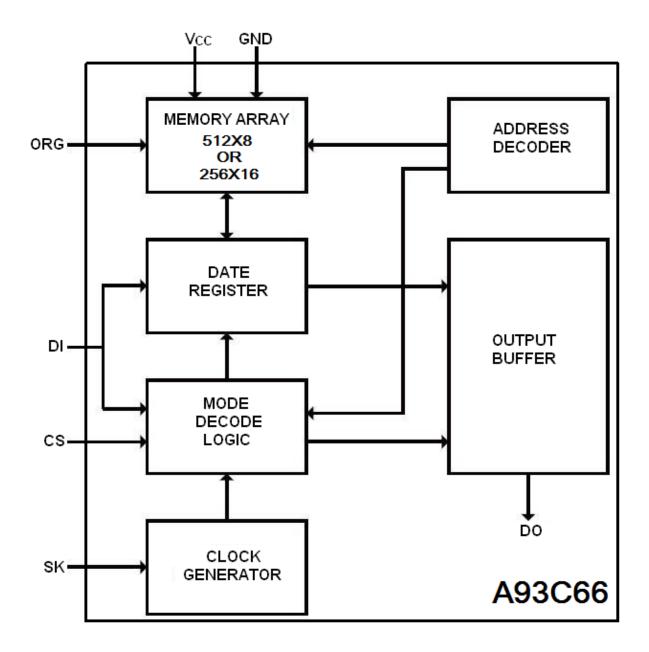
 T_A =-40°C to +85°C, V_{CC} =+1.8V to +5.5V, C_L =1 TTL Gate and 100pF, unless otherwise specified.

Parameter	Symbol	Condition		MIN	TYP	MAX	Unit
Faiailletei	Syllibol	1					Oilit
SK Clock Frequency	fsĸ		$8V \le V_{CC} \le 5.5V$	0	-	0.25	N 41 1—
			$7V \le V_{CC} \le 5.5V$	0	-	1	MHz
			$5V \le V_{CC} \le 5.5V$	0	-	2	
OK I I'd Time			$8V \le V_{CC} \le 5.5V$	1000	-	-	ns
SK High Time	t skh		$7V \le V_{CC} \le 5.5V$	250	-	-	
			$5V \le V_{CC} \le 5.5V$	250	-	-	
			$8V \le V_{CC} \le 5.5V$	1000	-	-	1
SK Low Time	t _{SKL}		$7V \le V_{CC} \le 5.5V$	250	-	-	ns
			5V ≤ V _{CC} ≤ 5.5V	250	-	-	
			$8V \le V_{CC} \le 5.5V$	1000	-	-	
Minimum CS Low Time	tcs		$7V \le V_{CC} \le 5.5V$	250	-	-	ns
			5V ≤ V _{CC} ≤ 5.5V	250	-	-	
			re to SK		Г	1	T
CS Setup Time	tcss		8V ≤ V _{CC} ≤ 5.5V	200	-	-	
CC Cotap Time	.000		7V ≤ V _{CC} ≤ 5.5V	50	-	-	ns
			5V ≤ V _{CC} ≤ 5.5V	50	-	-	
			re to SK	1	Г	1	T
DI Setup Time	tois		$8V \le V_{CC} \le 5.5V$	400	-	-	ns
- · · · · · · · · · · · · · · · · · · ·	LDIO		$7V \le V_{CC} \le 5.5V$	100	-	-	
0011117			5V ≤ V _{CC} ≤ 5.5V	100	-	-	
CS Hold Time	t csH	Relative to SK Relative to SK		0	-	-	ns
	t _{DIH}			400		1	
DI Hold Time			$8V \le V_{CC} \le 5.5V$		-	-	ns
			$7V \le V_{CC} \le 5.5V$ $5V \le V_{CC} \le 5.5V$	100 100	-	-	
		4.	$1.8V \le V_{CC} \le 5.5V$	-	-	1000	
Output Delay to "1"	ton.	AC	$1.6V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$	-	-	250	ne
Output Delay to 1	t _{PD1}	Test	$4.5V \le V_{CC} \le 5.5V$	_	_	250	ns
			$1.8V \le V_{CC} \le 5.5V$	_	_	1000	
Output Delay to "0"	t _{PD0}	AC	$2.7V \le V_{CC} \le 5.5V$	_	_	250	ns
Output Dolay to 0	trb0	Test	$4.5V \le V_{CC} \le 5.5V$	_	_	250	115
			$1.8V \le V_{CC} \le 5.5V$	_	_	1000	
CS to Status Valid	t sv	AC	$2.7V \le V_{CC} \le 5.5V$	_	_	250	ns
Co to Clatao vana		Test	$4.5V \le V_{CC} \le 5.5V$	_	_	250	115
		AC To		<u> </u>		230	
CS to DO in High Impedance		AC Test $C_S = V_{IL}$ $1.8V \le V_{CC} \le 5.5V$		_	_	400	
	t _{DF}		$7V \le V_{CC} \le 5.5V$	-	_	100	ns
			$5V \le V_{CC} \le 5.5V$	-	-	100	
Write Cycle Time	twp	<u>'</u>		-	1.5	5	ms
•							Write
5.0V, 25°C Endurance				1M	-	-	Cycles

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BLOCK DIAGRAM



When the ORG pin is connected to V_{CC} , the "x16" organization is selected. When it is connected to ground, the "x8" organization is selected. If the ORG pin is left unconnected and the application does not load the input beyond the capability of the internal 1 Meg ohm pull-up, then "x16" organization is selected.

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DETAILED INFORMATION

The A93C66 is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. A valid instruction starts with a rising edge of CS and consists of a start bit (logic"1") followed by the appropriate OP Code and the desired memory address location.

Instruction Set of A93C66

Instruction	ruction SB OP Address		Data		Comments			
motraotion		Code	x8	x16	x8	x16	- Commonto	
READ	1	10	A ₈ - A ₀	A ₇ - A ₀			Reads data stored in memory, at specified address	
EWEN	1	00	11XXXXXXX	11XXXXXX			Write enable must precede all programming modes	
ERASE	1	11	A ₈ - A ₀	A ₇ - A ₀			Erase memory location An - A ₀	
WRITE	1	01	A ₈ - A ₀	A ₇ - A ₀	D7 - D0	D ₁₅ - D ₀	Writes memory location An - A ₀	
ERAL	1	00	10XXXXXXX	10XXXXXX			Erases all memory locations. Valid only at V_{CC} = 4.5V to 5.5V	
WRAL	1	00	01XXXXXXX	01XXXXXX	D ₇ - D ₀	D ₁₅ - D ₀	Writes all memory locations. Valid only at V_{CC} = 4.5V to 5.5V	
EWDS	1	00	00XXXXXXX	00XXXXXX			Disables all programming instructions	

The X's in the address field represent don't care values and must be clocked.

READ (READ)

The Read (READ) instruction contains the address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 8- or 16-bit data output string. The A93C66 supports sequential read operations. The device will automatically increment the internal address pointer and clock out the next memory location as long as Chip Select (CS) is held high .In this case, the dummy bit (logic "0") will not be clocked out between memory locations, thus allowing for a continuous steam of data to be read.

ERASE/WRITE (EWEN):

To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable (EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the EWEN state, programming remains enabled until an EWDS instruction is executed or Vcc power is removed from the part.

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ERASE (ERASE)

The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1"state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250ns (T_{CS}). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE)

The Write (WRITE) instruction contains the 8 or 16 bits of data to be written into the specified memory location. The self-timed programming cycle, twp, starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250ns (Tcs). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. A Ready/Busy status cannot be obtained if the CS is brought high after the end of the self timed programming cycle, TWP.

ERASE ALL (ERAL)

The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250ns (T_{CS}). The ERAL instruction is valid only at V_{CC} = 5.0V \pm 10%.

WRITE ALL (WRAL)

The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250ns (T_{CS}). The WRAL instruction is valid only at V_{CC} = 5.0V ± 10%.

ERASE/WRITE DISABLE (EWDS)

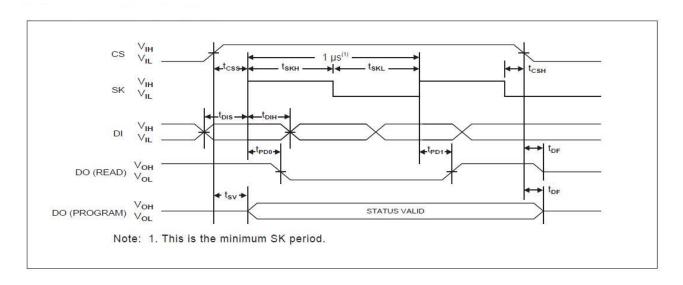
To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the Read instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

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TIMING DIAGRAMS

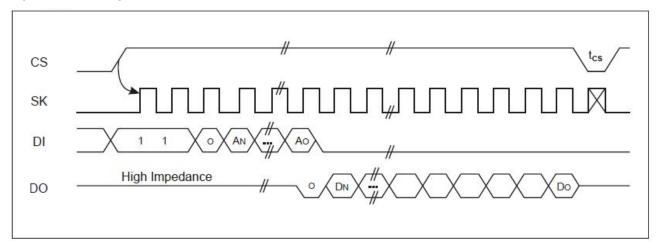
Fig1. Synchronous Data Timing



Organization Key for Timing Diagrams

I/O	A93C66(4K)				
	X 8	X 16			
AN	A8	A7			
DN	D7	D15			

Fig2. READ Timing



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Fig3. EWEN Timing

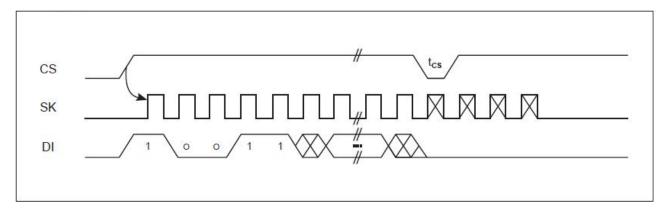


Fig4. EWDS Timing

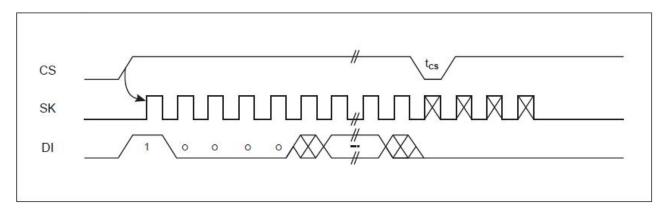
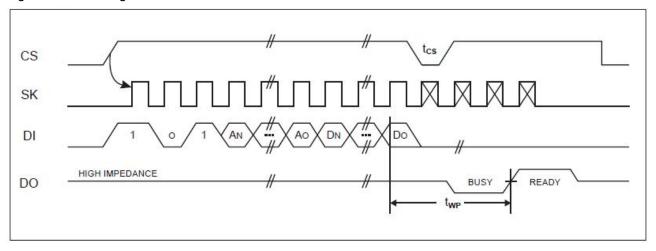


Fig5. WRITE Timing



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Fig6. WRAL Timing (Valid only at V_{CC}=4.5V to 5.5V)

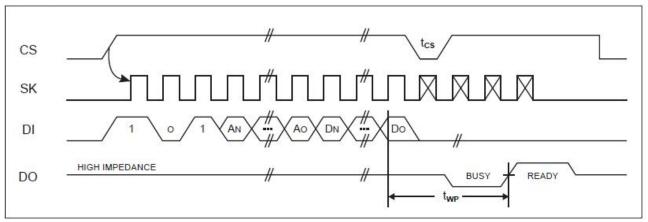


Fig7. ERASE Timing

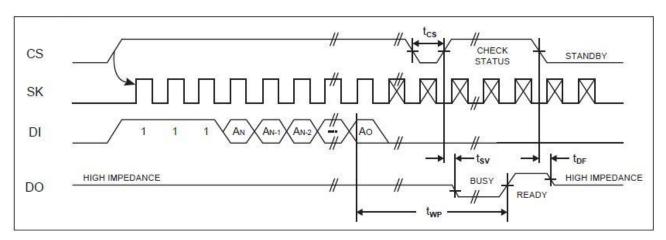
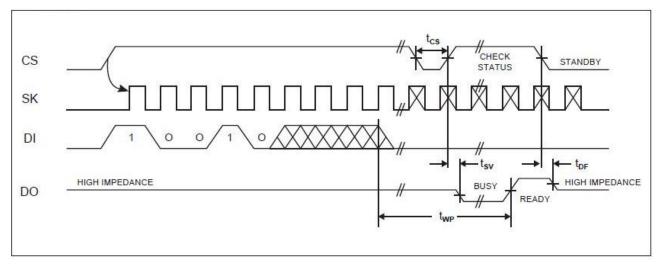


Fig8. ERAL Timing (Valid only at V_{CC} =4.5V to 5.5V)

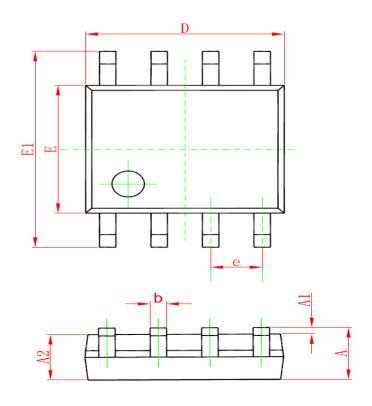


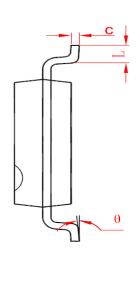
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PACKAGE INFORMATION

Dimension in SOP8 (Unit: mm)



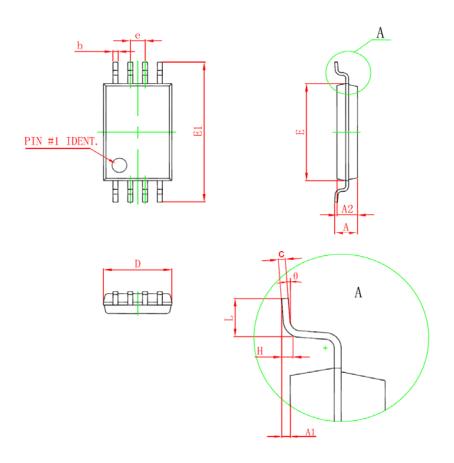


Symbol	Min	Max			
Α	1	1.770			
A1	0.080	0.280			
A2	-	1.770			
b	0.440	0.530			
С	0.210	0.260			
D	4.700	5.100			
Е	3.700	4.100			
E1	5.800	6.200			
е	1.270(BSC)				
L	0.400	1.270			
θ	0°	8°			

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Dimension in TSSOP8 (Unit: mm)



Symbol	Min	Max			
D	2.830	3.030			
Е	4.300	4.500			
b	0.200	0.280			
С	0.090	0.200			
E1	6.200	6.600			
А	-	1.200			
A2	0.900	1.050			
A1	0.050	0.150			
е	0.65 (BSC)				
L	0.450	0.750			
Н	0.25(TYP)				
θ	0°	8°			

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